

N-channel 100V 13.9mΩ standard level MOSFET in TO220. 10 August 2012 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	-	68	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics		I				
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 15 A; T _j = 100 °C; Fig. 12		-	19.4	25	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 13	[2]	-	10.8	13.9	mΩ
Dynamic ch	naracteristics	1		1	1		
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V; Fig. 15; Fig. 14		-	17	-	nC



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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Q _{G(tot)}	total gate charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V; <u>Fig. 14; Fig. 15</u>		-	59	-	nC
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} \texttt{=} 10 \; V; \; T_{j(\text{init})} \texttt{=} 25 \; ^{\circ}\text{C}; \; I_{D} \texttt{=} 68 \; A; \\ V_{sup} \texttt{\leq} 100 \; V; \; unclamped; \; R_{GS} \texttt{=} 50 \; \Omega \end{array}$		-	-	128	mJ

Continuous current is limited by package Measured 3 mm from package. [1]

[2]

2. **Pinning information**

Pin	Sumbal	Description	Cimulified outline	Craphia aymhal
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain	204	
3	S	source		G - U - T - T - T - T - T - T - T - T - T
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

Ordering information 3.

Table 3. Ordering int	formation					
Type number	Package	ge				
	Name	Description	Version			
PSMN013-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

Marking 4.

Table 4. Marking codes	
Type number	Marking code
PSMN013-100PS	PSMN013-100PS

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5. Limiting values

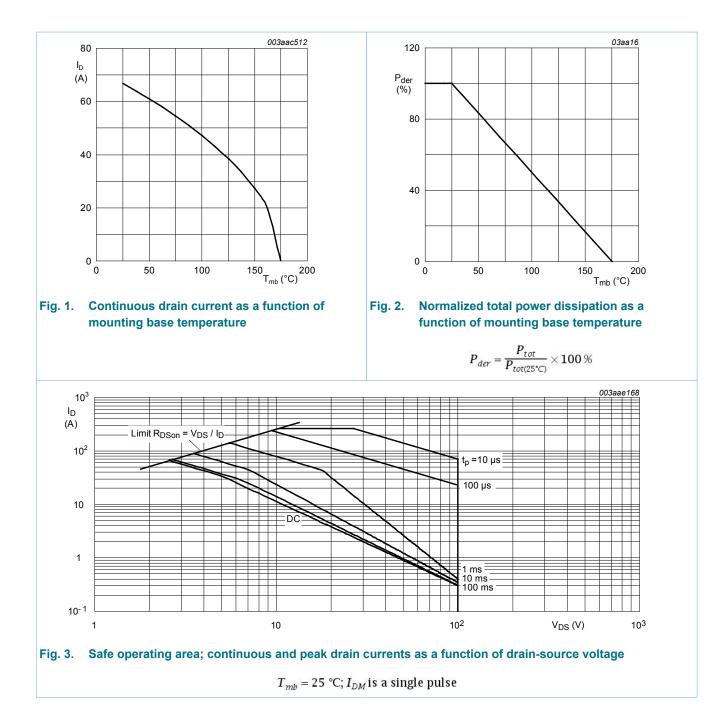
Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	[1]	-	47	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	68	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	272	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	170	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	68	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	272	А
Avalanche	ruggedness	,				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy			-	128	mJ

[1] Continuous current is limited by package

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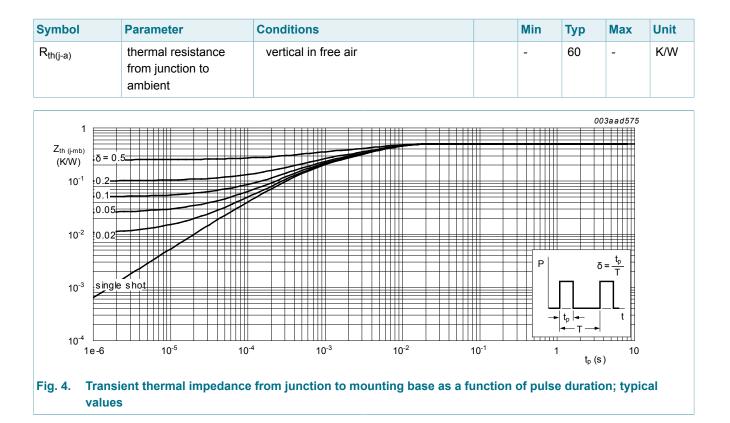
6. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.5	0.9	K/W

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7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·				
V _{(BR)DSS}	drain-source	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.6	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C	-	-	100	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.06	2	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; Fig. 12	-	19.4	25	mΩ

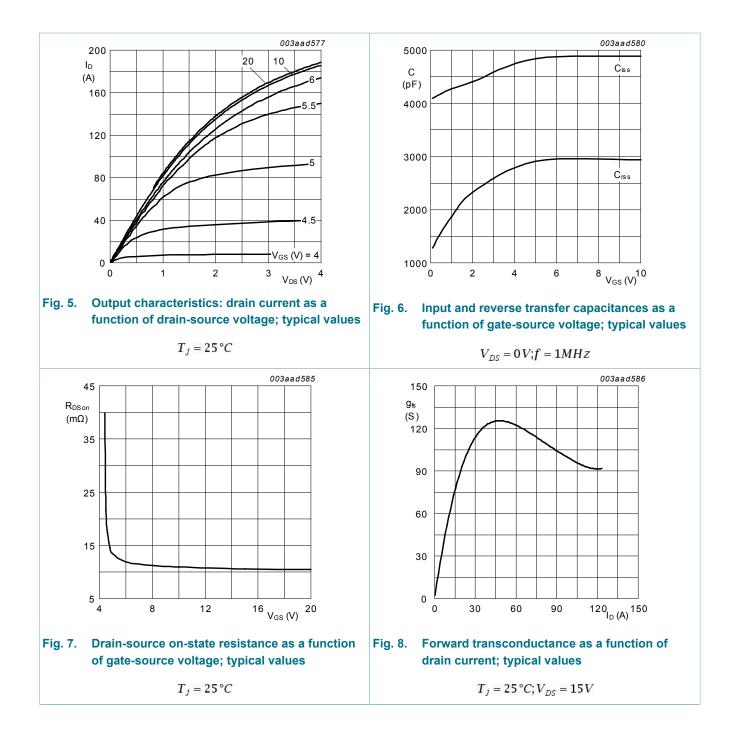
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; <u>Fig. 12</u>		-	29.5	38.9	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 13</u>	[1]	-	10.8	13.9	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz		-	1	-	Ω
Dynamic ch	naracteristics						
Q _{G(tot)} total gate charge		I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 14; Fig. 15		-	59	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$		-	47.6	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 14; Fig. 15		-	13.8	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 15		-	9.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate- source charge			-	4.6	-	nC
Q _{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 15; Fig. 14		-	17	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; <u>Fig. 15; Fig. 14</u>		-	4.4	-	V
C _{iss}	input capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz;		-	3195	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>		-	221	-	pF
C _{rss}	reverse transfer capacitance	-		-	136	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; R_L = 2 Ω ; V_{GS} = 10 V;		-	20.7	-	ns
t _r	rise time	R _{G(ext)} = 4.7 Ω; T _j = 25 °C		-	25	-	ns
t _{d(off)}	turn-off delay time			-	52.5	-	ns
t _f	fall time			-	24	-	ns
Source-dra	in diode			1			
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u>		-	0.85	1.2	V
t _{rr}	reverse recovery time	I_{S} = 25 A; dI _S /dt = 100 A/µs; V _{GS} = 0 V;		-	52	-	ns
Qr	recovered charge	V _{DS} = 50 V		-	109	-	nC

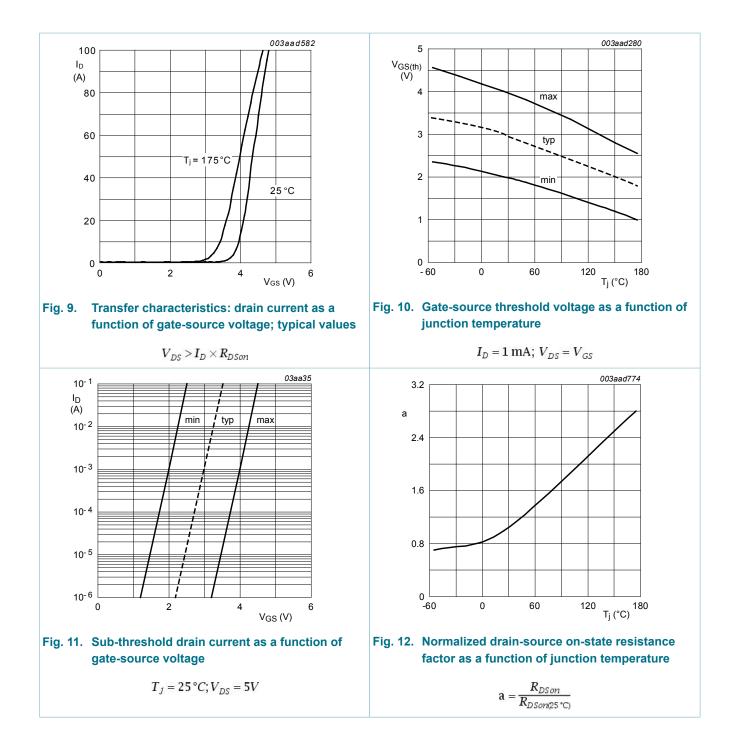
[1] Measured 3 mm from package.

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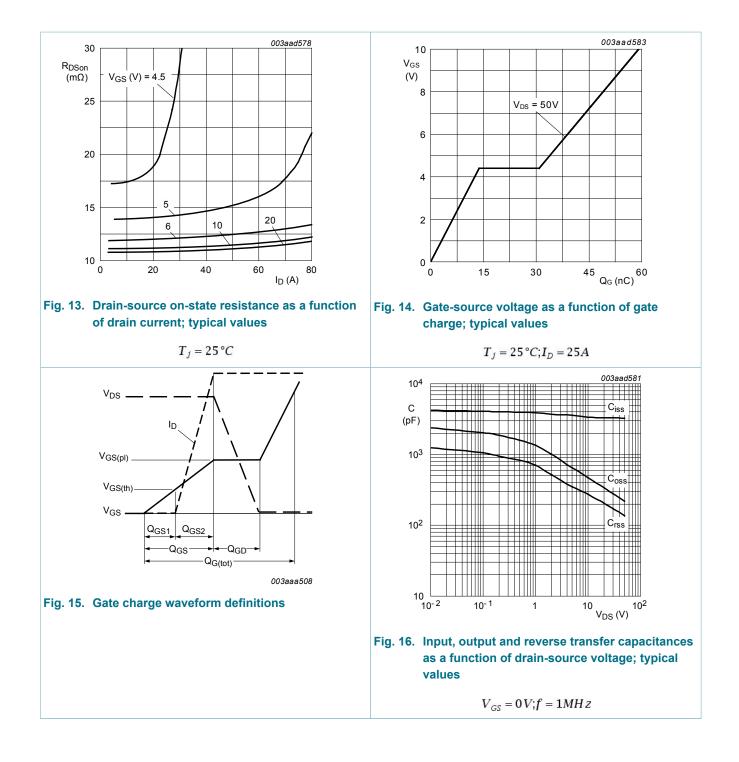
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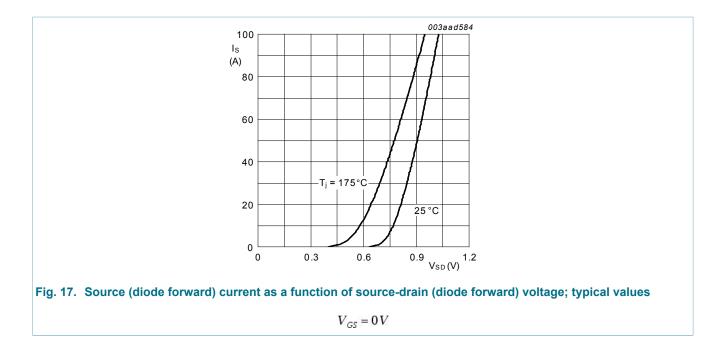


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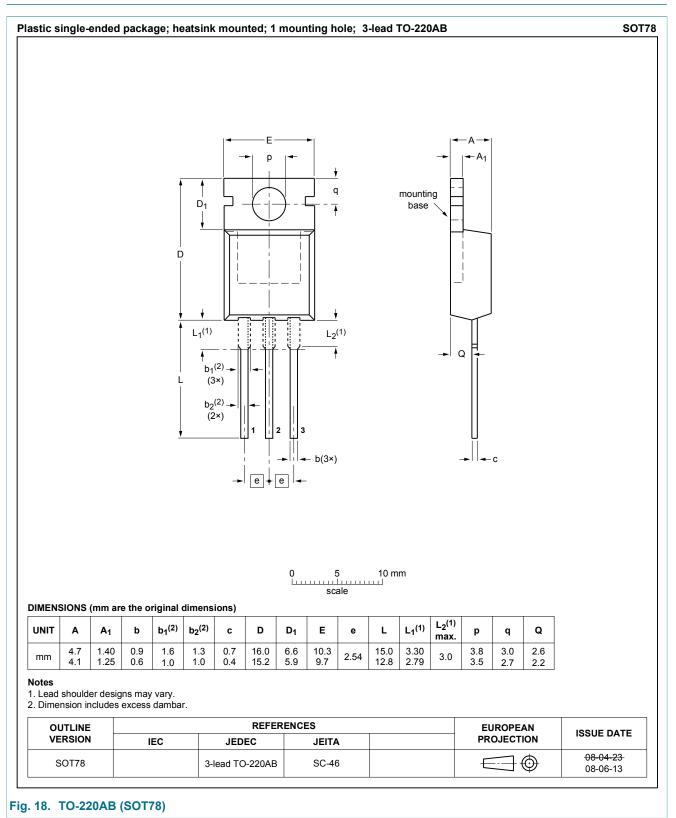
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8. Package outline



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9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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